

DOCKET NO. GEVA 6-2-4-21

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Michael Geva, *et al.*

Serial No.: 09/757,099

Filed: January 8, 2001

For: ELECTRONIC DEVICE HAVING A BARRIER REGION  
INCLUDING ALUMINUM AND A METHOD OF MANUFACTURE  
THEREFOR

Group No.: 2874

Commissioner for Patents  
Washington, D. C. 20231

Sir:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on 7/17/2001 (Date)  
Elizabeth Schumacher  
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(Signature of the person signing the certificate)  
7-17-2001  
(Date of Signature)

INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. §1.56 and the provisions of 37 C.F.R. §§1.97 and 1.98 and §609 of the Manual of Patent Examining Procedure, Applicant hereby makes a disclosure of the patents, publications and other information listed below and on the accompanying form PTO-1449, which may be potentially material to the patentability of the invention disclosed in the above-



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referenced application. Pursuant to § 1.97(e) the Applicant hereby states that each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

<u>U.S. Patent No.</u>	<u>Inventor</u>	<u>Date</u>
5,882,951	Bhat	March 16, 1999
5,559,910	Taga et al.	September 24, 1996
4,438,446	Tsang	March 20, 1984

<u>Foreign Patent No.</u>	<u>Country</u>	<u>Date</u>
97/50133	WO	31 December 1997
97/40560	WO	30 October 1997
0 715 380 A1	EP	5 June 1996
0 557 638 A2	EP	1 September 1993
0 518 320 A2	EP	16 December 1992

Ref:

K. Schimpf, J. Hollfelder, M. Horstmann, M. Marso, H. Hardtdegen and P. Kordos; "0.2um T-gate InP/InGaAs/InP pHEMT with InGaP diffusion barrier layer grown by LP-MOCVD using and N<sub>2</sub>-carrier"; IPRM, SCHWABISCH-GMUND, 1996, pgs. 666-669 XP-002169035.

Applicant hereby certifies that each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the statement.

As attorney for the Applicant, I am signing below on the basis of the information supplied  
by an individual designated in § 1.56(c).

Respectfully submitted,

HITT GAINES & BOISBRUN, P.C.

A handwritten signature in cursive script, appearing to read "Charles W. Gaines", is written over a horizontal line.

Charles W. Gaines  
Registration No. 36,804

Date: 7/17/01

Hitt Gaines & Boisbrun, P.C.  
P.O. Box 832570  
Richardson, Texas 75083  
(972) 480-8800